Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- · ElectroStatic Discharge (ESD) protection
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V	
V _{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	220	mA	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$		-	2.2	3	Ω	

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1		D1 D2
2	G1	gate 1	654	
3	D2	drain 2		G1 A A A BLANCE
4	S2	source 2	0	\
5	G2	gate 2	1 2 3	
6	D1	drain 1	TSSOP6 (SOT363)	S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
2N7002AKS-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
2N7002AKS-Q	Ј2%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or			'		
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	220	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	160	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.8	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	270	mW
			[1]	-	310	mW
		T _{sp} = 25 °C		-	1.3	W
Per device	'					
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	405	mW
T _j	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source Drain	n Diode (per transistor)			'	'	'
I _S	source current	T _{amb} = 25 °C	[1]	-	210	mA
ESD maximu	um rating (per transistor)			,	'	
V _{ESD}	electrostatic discharge voltage	НВМ		-	500	V
Avalanche ru	uggedness (per transistor)					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 20 mA; DUT in avalanche (unclamped)		-	6.6	mJ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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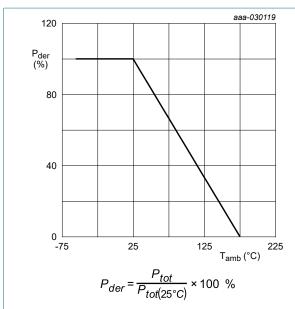


Fig. 1. Normalized total power dissipation as a function of ambient temperature

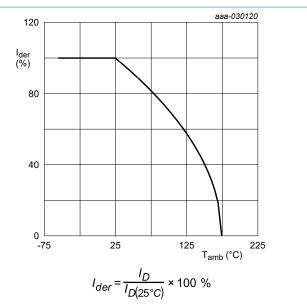


Fig. 2. Normalized continuous drain current as a function of ambient temperature

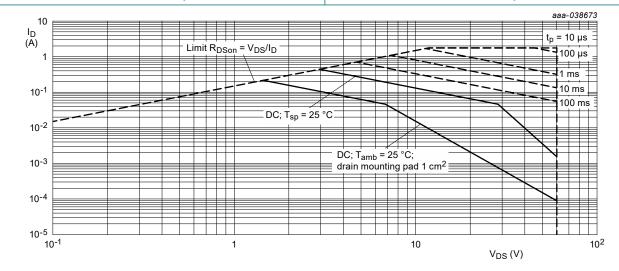


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	375	K/W
Per transisto	or						
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	500	560	K/W
	junction to ambient		[2]	-	450	480	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	98	115	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

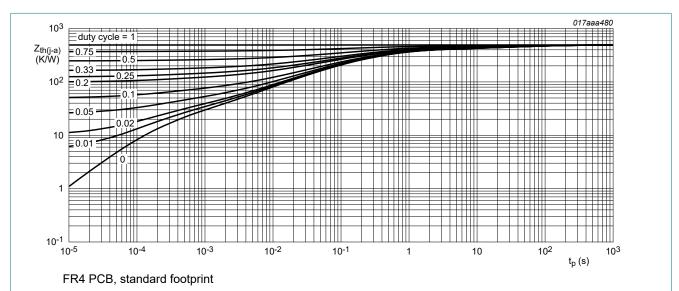


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

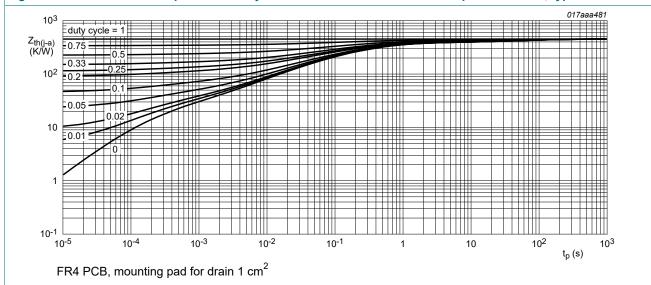


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \degree C$	1.3	1.7	2.6	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	500	nA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 125 °C	-	-	5	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	500	nA
		$V_{GS} = -5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-500	nA
R _{DSon} drain-source resistance	drain-source on-state	V _{GS} = 10 V; I _D = 100 mA; T _j = 25 °C	-	2.2	3	Ω
	resistance	V _{GS} = 10 V; I _D = 100 mA; T _j = 175 °C	-	4.7	6.7	Ω
		V _{GS} = 5 V; I _D = 50 mA; T _j = 25 °C	-	2.5	3.6	Ω
9 _{fs}	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$	-	0.3	-	S
Dynamic ch	naracteristics		,			
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 100 mA; V _{GS} = 10 V;	-	0.21	0.315	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.022	-	nC
Q _{GD}	gate-drain charge		-	0.051	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	9.2	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	1.6	-	pF
C _{rss}	reverse transfer capacitance		-	0.9	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; I _D = 100 mA; V _{GS} = 10 V;	-	1	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	1	-	ns
t _{d(off)}	turn-off delay time]	-	2	-	ns
t _f	fall time		-	6	-	ns
Source-dra	in diode		'		•	
V_{SD}	source-drain voltage	$I_S = 210 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	1	1.6	V
t _{rr}	reverse recovery time	$I_S = 210 \text{ mA}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	7	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	1	-	nC

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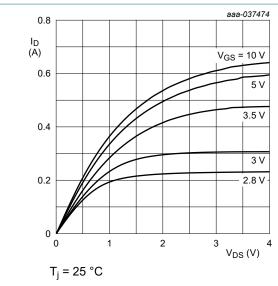


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

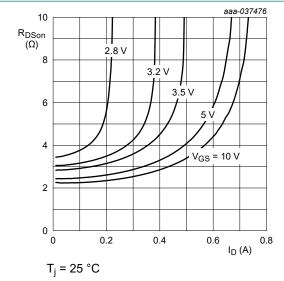


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

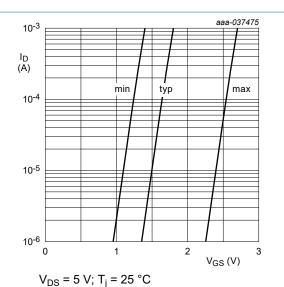


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

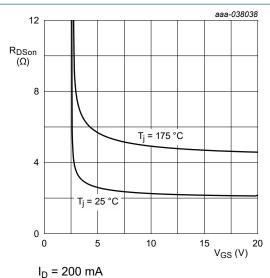


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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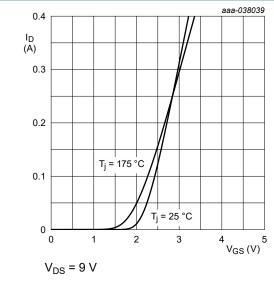


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

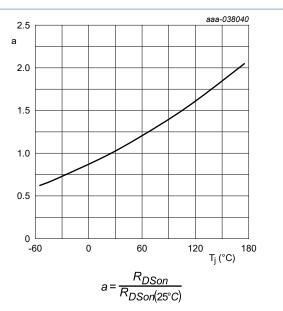


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

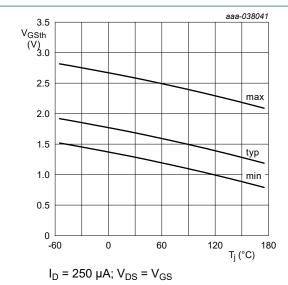
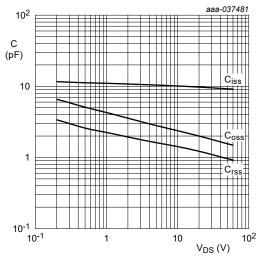


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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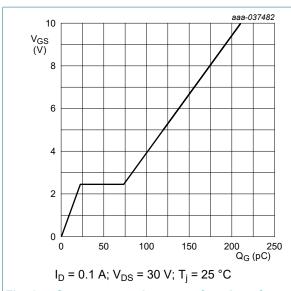


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

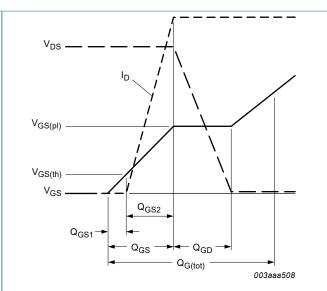


Fig. 15. Gate charge waveform definitions

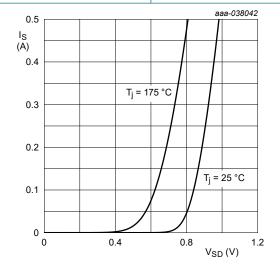
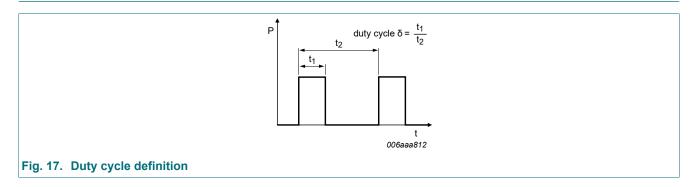


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

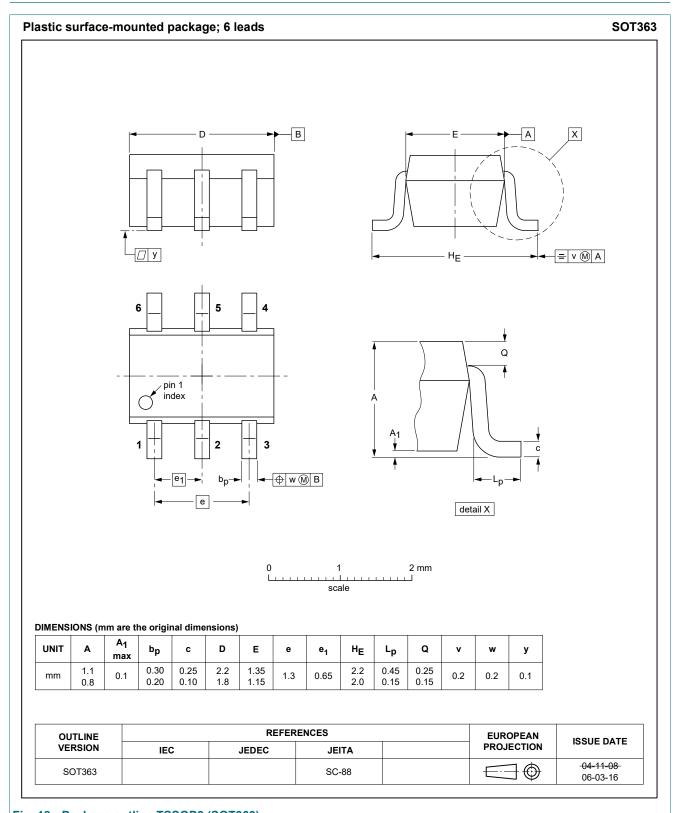
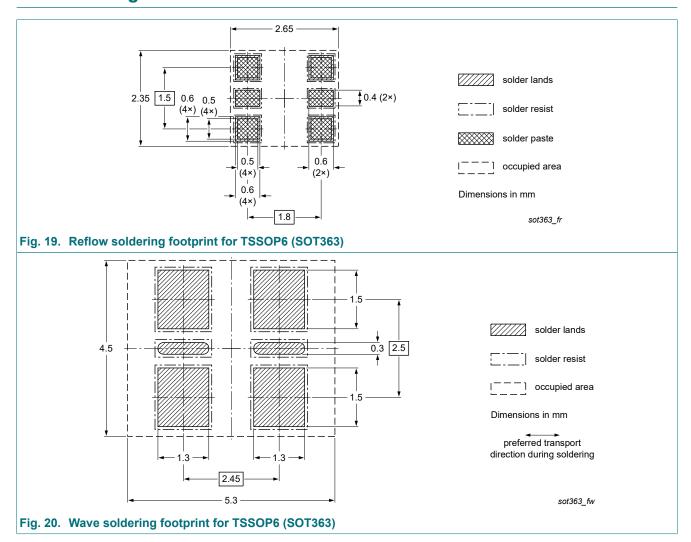


Fig. 18. Package outline TSSOP6 (SOT363)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
2N7002AKS-Q v.1	20240216	Product data sheet	-	-

60 V, dual N-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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